

QLF063A-4080T30/QLF063D-4080T30

640 nm 80mW FP LASER TO-CAN, Tc=30deg.C

C00127-03 March 2021



1. DESCRIPTION

The QLF063A-4080T30 is a 640 nm quantum well laser device designed for visible laser application. The laser diode is mounted into a TO-56 header including a monitor PD and hermetic sealed with a flat glass cap.

FEATURES

- 640 nm FP-LD
- Operating temperature range=-10 to 30deg.C
- Φ5.6mm TO-CAN package
- Including monitor PD
- Two types of pin assignments: anode common type (QLF063A-4080T30) cathode common type (QLF063D-4080T30)

APPLICATIONS

- Industrial laser markers
- Measuring instruments

ABSOLUTE MAXIMUM RATING

(CW operation, $T_c = 25^{\circ}$ C, unless otherwise specified)

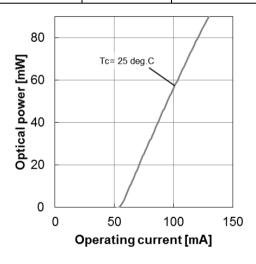
PARAMETER	SYMBOL	RATING	UNIT
Optical output power	P _o (CW)	90	mW
LD reverse voltage	V_{RLD}	2	V
PD reverse voltage	V_{RPD}	30	V
Operation temperature	Tc	-10 to 30	°C
Storage temperature	$T_{ m stg}$	-40 to 85	°C

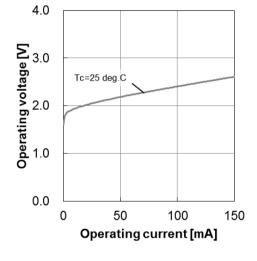


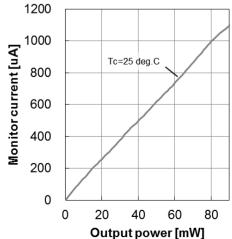
vertical

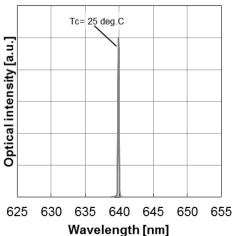
5. OPTICAL AND ELECTRICAL CHARACTERISTICS

			$(T_c = 25^{\circ}C, unless otherwise specified)$			
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold current	I_{th}	CW	1	60	100	mA
Operation current	I _{op} (CW)	CW, P _o =80mW	-	135	160	mA
Operation voltage	V_{op}	CW, P _o =80mW	-	2.4	3.2	V
Slope efficiency	η	CW, P _o =5 - 80mW	0.8	1.0	-	W/A
Monitor current	I_{m}	CW , P_o =80 mW , V_{RD} =5 V	400	1000	1800	μΑ
Peak wavelength	λ_{p}	CW, P _o =80mW	635	641	650	nm
Far filed pattern horizontal	θ_{h}	CW, P _o =80mW	4	7	13	deg.
Far filed pattern vertical	$\theta_{ m v}$	CW, P ₀ =80mW	11	15	22	deg.
Beam angle Horizontal	$d\theta_h$	CW, P _o =80 mW	-3	-	3	deg.
Beam angle	$d\theta_v$	CW. P _o =80 mW	-3	-	3	deg.



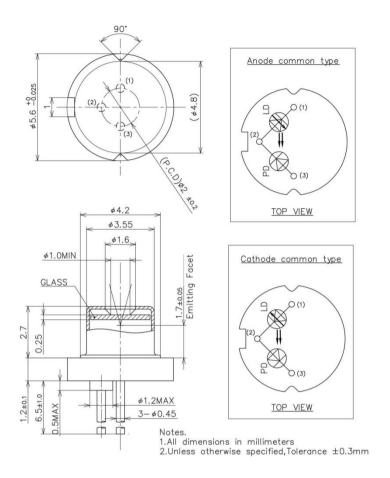








Outline Drawing



Notice

Safety Information

This product is classified as Class 3B laser product, and complies with 21 CFR Part 1040.10. Please do not take a look laser lighting in operations since laser devices may cause troubles to human eyes. Please do not eat, burn, break and make chemical process of the products since they contain GaAs material.

Handling products

Semiconductor lasers are easily damaged by external stress such as excess temperature and ESD. Please pay attention to handling products, and use within range of maximum ratings. QD Laser takes no responsibility for any failure or unusual operation resulting from improper handling, or unusual physical or electrical stress.

RoHS

This product conforms to RoHS compliance related Directive (EU) 2015/863.

QD Laser, Inc.

Contact: info@qdlaser.com http://www.qdlaser.com

Copyright 2014-2021 All Rights Reserved by OD Laser Inc.

Address: Keihin Bldg.1F 1-1 Minamiwataridacho, Kawasaki-ku, Kawasaki, Kanagawa Zip 210-0855 Japan

All company or product names mentioned herein are trademarks or registered trademarks of their respective owners. Information provided in this data sheet is accurate at time of publication and is subject to change without advance notice.

